BIRLA INDUSTRIAL & TECHNOLOGICAL MUSEUM

(A unit of National Council of Science Museums) 19A, Gurusaday Road, Kolkata – 700 019

Written Test for recruitment of Technician 'A' (Electronics) at BITM, Kolkata

Date: 03.03.2023			Marks: 30 Time: 1 hour
Roll No:		Sig	dinamina ny arangan'i Ny arangana ny grature:
			CONTRACTOR
General Instructions:			
2. To answer objective from the 3 alternative	type questions put a $()$ markers given below against each	k on the correct ar	nswer in the question paper itself
3. To change answer, p	out (X) on previous answer ar	$\operatorname{id}(\sqrt[4]{})$ the fresh an	nswer. Hiji fan jarag gaar tit it
	watch are to be put on switche		
5. There is no negative marking.			
Coloot the wight alternat		$\frac{\mathbf{n} - \mathbf{A}}{\mathbf{A}}$	
Select the right alternat	ive:		$(10 \times 1) = 10$
1. In a pure Inductor the	Current lags Voltage by:		
a. 90°	b. 180°	c. 270°	
2. A Capacitor stores ene	rgy in the form of:		
a. Current	b. Voltage	c. Depends or	n DC Resistance across the terminals
3. A Rectifier Diode has a	a Peak Inverse Voltage (PIV)	of 12 Volts:	osofa Kozza den presidanja se je og
a. Forward current will	l start flowing if it is forward	biased with 5 Vo	
b. Forward current will	l start flowing if it is reverse	biased with a Vol	tage of 5 Volts
c. None of the above			
4. Other than rectifiers. Se	emiconductor Diodes are also	ag <i>director</i>	医神经囊性性 医皮肤 医皮肤皮肤 医皮肤 医耳氏管
	ak NAVAH QHILI MARÉTI Jak	rused III. Prymos et an Gilb	
a. Shift Registers	b. Envelope Detectors	c. Low Pass F	ilters to a very many many and a company of
5. BJT can be used for:			
. Current Amplification	b. Amplitude Modulation	c. Both the ab	ove

- 6. Uni Junction Transistors used to have:
 - a. Negative Resistance Region in its Current vs. Voltage characteristics
 - b. Energy Storage ability in its junction
 - c. Temperature Independent Functioning
- 7. MOSFET stands for:
 - a. Metal Oxide Semiconductor Forward Effect Transistor
 - b. Multiple Oxide Semiconductor Forward Effect Transistor
 - c. Metal Oxide Semiconductor Field Effect Transistor
- 8. For a Switching Circuit that operates in 10 MHz, you will prefer to use:
 - a. A BJT over a MOSFET
 - b. Both BJT and MOSFET with equal preference
 - c. A MOSFET over a BJT
- 9. MOSFET is an example of a:
 - a. Voltage Controlled Device
 - b. Current Controlled Device
 - c. Magnetically Coupled Device
- 10. All other Digital Logic Gates can be designed with the help of:
 - a. NAND Gates, not NOR Gates
 - b. NOR Gates, not NAND Gates
 - c. Both NAND Gates and NOR Gates

Section - 'B'

Write Short Notes on any 5 of the Following:

 $(5 \times 4) = 20$

- 1. Name of at least 4 different types of Diodes along with their application
- 2. Design OR Gate using NAND Gate
- 3. Design AND Gate using NOR Gate
- 4. Symbol and Truth Table of XOR Gate
- 5. Switched Mode Power Supply
- 6. Bluetooth Audio Amplifier